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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10729,095
				Filing Date	December 5, 2003
				First Named Inventor	Ko, et al.
				Art Unit	2818
				Examiner Name	TBD
Sheet	1	of	5	Attorney Docket Number	TSM03-0615

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
✓	1	US-4,314,269	02-02-1982	Fujiiki	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-4,946,799	08-07-1990	Blake, et al.	
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	6	US-5,534,713	07-09-1996	Ismail, et al.	
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	9	US-5,763,315	06-09-1998	Benedict, et al.	
	10	US-5,811,857	09-22-1998	Assaderaght, et al.	
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	21	US-6,387,739 B1	05-14-2002	Smith, III	
✓	22	US-2002/0076899 A1	06-20-2002	Skotnicki, et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
V ₂	23	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

Examiner Signature	HUNG JU	Date Considered	07/05/05
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				First Named Inventor	Ko, <i>et al.</i>
				Group Art Unit	2818
				Examiner Name	TBD
				Attorney Docket Number	TSM03-0615
Sheet	3	of	5		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cita. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		1 ²
✓	40	ISMAIL, K, <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.		
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	44	MIZUNO, T., <i>et al.</i> , "Novel SOI p-Channel MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, Vol. 49, No. 1, (January 2002), pp. 7-14.		
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Examiner Signature		HUNG VU	Date Considered	07/05/05

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/729,095
				Filing Date	December 5, 2003
				First Named Inventor	Ko, <i>et al.</i>
				Group Art Unit	2818
				Examiner Name	TBD
Sheet	4	of	5	Attorney Docket Number	TSM03-0615

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²	
<u>Vu</u>	53	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.			
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<u>Vu</u>	65	YEOH, J.C., <i>et al.</i> , "MOS Gated Si:SiGe Quantum Wells Formed by Anodic Oxidation," Semicond. Sci. Technol. (1998), Vol. 13, pp. 1442-1445, IOP Publishing Ltd., UK.			
Examiner Signature	HUNG VU			Date Considered	07/05/05

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		Examiner Name	TBD		
Sheet	5	of	5	Attorney Docket Number	TSM03-0615

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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✓	66	CAVASSILAS, N., <i>et al.</i> , "Capacitance-Voltage Characteristics of Metal-Oxide-Strained Semiconductor Si/SiGe Heterostructures," Nanotech 2002, Vol. 1, pp. 600-603.	
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✓	70	CHANG, L., <i>et al.</i> , "Direct-Tunneling Gate Leakage Current in Double-Gate and Ultrathin Body MOSFETs," 2002 IEEE, Vol. 49, No. 12, December 2002.	

Examiner Signature	HUNG JU	Date Considered	07/05/05
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Application Number	10/729,095
Filing Date	December 5, 2003
First Named Inventor	Ko, et al.
Art Unit	2818 2811
Examiner Name	TBD H. Vu
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Sheet	1	of	2
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Vu	13	LEITZ, C.W., et al., "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," Materials Research Society Symposium Proceedings, vol. 686, (2002), pp. 113-118.	
Vu	14	LEITZ, C.W., et al., "Hole mobility enhancements in strained Si/Si _{1-x} Ge _x p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si _{1-x} Ge _x (x<y) virtual substrates," Applied Physics Letters, Vol. 79, No. 25, pp. 4246-4248, December 17, 2001.	
Vu	15	LIU, K.C., et al., "A Novel Sidewall Strained-Si Channel nMOSFET," IEDM, (1999) pp. 63-66.	

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				Art Unit	2811
				Examiner Name	Vu, Hung K.
				Attorney Docket Number	TSM03-0515
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Vu	1	US-5,155,571	10-13-1992	Wang, et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/729,095
				Filing Date	December 5, 2003
				First Named Inventor	Ko, et al.
				Art Unit	2811
				Examiner Name	Hung K. Vu
Sheet	1	of	1	Attorney Docket Number	TSM03-0615

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✓	1	US-6,833,070 B2	10-14-2003	Miura, et al.	
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